Calculating the gain of the transistor for noise margin.  $g = \frac{dV_{\text{out}}}{dV_{\text{in}}}$ Note: - Around Vm, both NFET and PFET are saturated. IPFET = INFET always in D.C. INFET = 2 Bn [Vin-VTN] [1+ An Vout] IPFET = 1 BP [VDD- VIN - |VTP]] [1+ |Ap] (VD) - Vout) Leto take dvout for NFET First 1 Bn [Vin VTN] [ In dVove ] + Bn [l+ In Vove ] [Vin-1/TN] 1 BP [VDD-VIN-IVTP]] [- 1) Pl dVovt ]- BP [I+ 1) (VDD-Vovt)] [VOD-VIN- [VTP]] Now taking Avois For PFET Now use Vin ~ Vm.

Substituting this in dVoit for the NFET device 1 Bu [Vm- VTN] [ In dVout ] + Bu [Vm- VTN] [I+ InVovt] equel to J2 Ip (Vm) Bn Note that this is the current of NFET/PFET at threshold Ib (Vm) [du dVort] + (ZBuIb(Vm) [l+ duVout] I, (Vm) 1/2 BP [VDD-VM-|VTP] [- | API dVout ] - BP [VDD-VM-|VTP] [1+ 1API (VDD-Vout)] Substituting Vin= Vm in the equation for PFET ID (Vm) In dVout + (2 ID (Vm) Bn [1+ Invout] Weaplest ID (Vm) Putting everything together, we have =-T. (Vm) []p| dVout - [ZIOVm) BP [+ 1 /p] (VD)

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$$T_{D}(V_{m}) \stackrel{\text{def}}{=} \frac{1}{dV_{in}} = -T_{D}(V_{m}) \left[ \frac{1}{dV_{in}} - \frac{1}{2} \frac{1}{dV_{in}} \right] = -T_{D}(V_{m}) \stackrel{\text{def}}{=} \frac{1}{dV_{in}} \stackrel{\text{def}$$